NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI 2N6199** is Designed for VHF Class C Power Amplifier Applications up to 250 MHz.

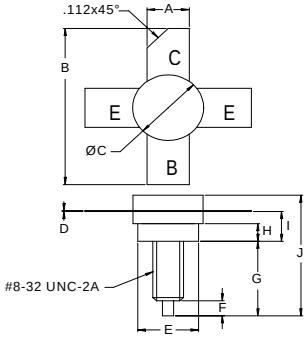
FEATURES:

- P_G = 10 dB Typical at 25 W/175 MHz
- ∞ Load VSWR at Rated Conditions
- ***Omnigold***™ Metallization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CB}	65 V
P_{DISS}	40 W @ T_C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +150 °C
θ_{JC}	4.4 °C/W

PACKAGE STYLE .380" 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10864

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 200 mA	65			V
BV_{CEO}	I_C = 200 mA	35			V
BV_{EBO}	I_E = 10 mA	4.0			V
I_{CBO}	V_{CB} = 30 V			2.0	mA
h_{FE}	V_{CE} = 5.0 V I_C = 200 mA	10			---
C_{ob}	V_{CB} = 28 V f = 1.0 MHz			50	pF
P_G η_c	V_{CE} = 28 V P_{OUT} = 25 W f = 175 MHz	8.5 50	10 60		dB %

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Specifications are subject to change without notice.